

2560 BITS (256x10) MOS Read Only Memory

MOSTEK

FEATURES

- Ion-implanted for full TTL/DTL compatibility
- Chip enable permits wire-ORing
- Custom-programmed memory requires single mask modification
- 550 ns cycle time ($0^\circ \leq T_A \leq 75^\circ\text{C}$)
- Static output storage latches
- Optional 3-bit, chip-select decoder available
- 2560 bits of storage, organized as 256 10-bit words
- Operates from +5V and -12V supplies

APPLICATIONS

- Look-up table
- Code converter
- Stroke character generator
- Dot-matrix character generator

DESCRIPTION

The MK 2400 P Series TTL/DTL-compatible MOS Read-Only Memories (ROM's) are designed for a wide range of general-purpose memory applications where large quantity bit storage is required. Each ROM provides 2560 bits of programmable storage, organized as 256 words of 10 bits each. Low threshold-voltage processing, utilizing ion implantation with P-channel enhancement-mode MOS technology, provides direct input/output interface with TTL and DTL logic.

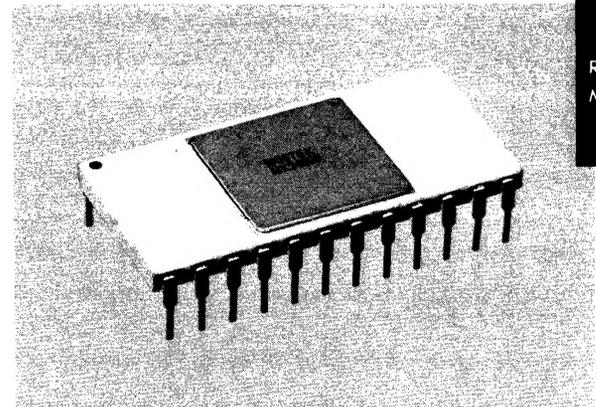
Programming is accomplished during manufacture by modification of a single mask, according to customer specifications. The MK 2400 P Series is available in either 24-lead or 28-lead ceramic dual-in-line packages. On the 28-pin ROM, an optional Chip Select Decoder may also be programmed according to customer specifications to provide a 3-bit Chip Select Code.

For additional information regarding custom programming and coding sheets, contact your nearest Mostek representative.

Operation involves transferring addressed information from the memory matrix into the storage latches using the READ and $\overline{\text{READ}}$ inputs (see Timing). Information stored in the latches will remain despite address changes or chip disabling until the READ and $\overline{\text{READ}}$ inputs are again cycled. READ and $\overline{\text{READ}}$ input signals may be generated from separate timing circuits if desired, or either may be the inverse of the other.

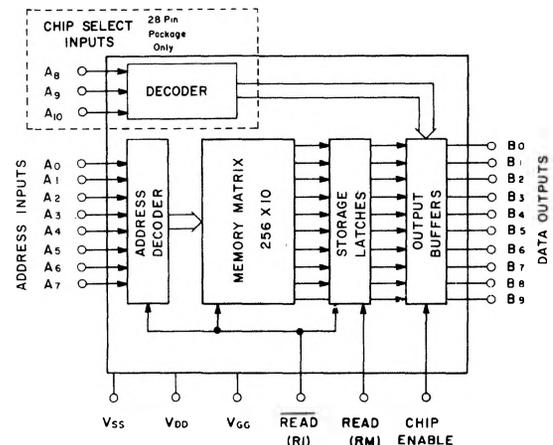
The Chip Enable input forces the normally push-pull output buffer stages to an open-circuit condition when disabling the chip. If desired, new data can be stored in the storage latches while the chip is disabled. When the chip is re-enabled, this data would be present at the outputs.

All inputs are protected against static charge accumulation. Pull-up resistors on all inputs are available as a programmable option.



Read Only Memories

FUNCTIONAL DIAGRAM



OPERATING NOTES

CHIP ENABLE	READ	$\overline{\text{READ}}$	OUTPUT
0	X	X	A
1	0	1	B
1	1	0	C

"1" = V_{SS} (+5V); "0" = V_{DD} (0V)

X = No effect on output

A = Output open-circuited

B = Output retains data last stored in latches

C = Output assumes state of addressed cells

ABSOLUTE MAXIMUM RATINGS

Voltage on any terminal relative to V_{SS} +0.3V to -10V
 Operating temperature range..... 0°C to +75°C
 Storage temperature range..... -55°C to +150°C

RECOMMENDED OPERATING CONDITIONS ($0^{\circ}\text{C} \leq T_A \leq 75^{\circ}\text{C}$)

	PARAMETER		MIN	TYP	MAX	UNITS	COMMENTS
POWER	V_{SS}	Supply voltage	+4.75	+5.0	+5.25	V	See note 1
	V_{DD}	Supply voltage	—	0.0	—	V	
	V_{GG}	Supply voltage	-12.6	-12.0	-11.4	V	
INPUTS	$V_{in(0)}$	Input voltage, logic "0"	$V_{SS}-1.5$	0	+0.8	V	Pull-up resistors ($\approx 5K\sim$) to V_{SS} available as programmable option.
	$V_{in(1)}$	Input voltage, logic "1"		V_{SS}			
INPUT TIMING	t_{cyc}	Address change cycle time	550			ns	See Timing Section
	t_{id}	Address to $\overline{\text{Read}}$ lead time	250			ns	
	t_{ig1}	Read lag time 1	-0.5		.05	μs	
	t_{ig2}	Read lag time 2	-0.5		.05	μs	
	$t_{r\overline{d}}$	$\overline{\text{Read}}$ pulse width	300			ns	
	$t_{r,d}$	Read pulse width	0.3		100	μs	
	t_r	Rise time, any input			100	ns	
	t_f	Fall time, any input			100	ns	

ELECTRICAL CHARACTERISTICS ($V_{SS} = +5.0\text{V} \pm 0.25\text{V}$, $V_{GG} = -12.0\text{V} \pm 0.6\text{V}$, $0^{\circ}\text{C} \leq T_A \leq +75^{\circ}\text{C}$, unless noted otherwise. Pull-up resistors not programmed.)

	PARAMETER		MIN	TYP*	MAX	UNITS	CONDITIONS
POWER	I_{SS}	Supply current (V_{SS})		12	25	mA	Outputs unconnected
	I_{GG}	Supply current (V_{GG})		-12	-25	mA	See Note 2 and Note 3
INPUTS	C_{in}	Input capacitance		5	10	pF	$V_{in} = V_{SS}$, $f_{meas} = 1\text{MHz}$
	I_{in}	Input leakage current			10	μA	$V_{in} = V_{SS} - 6\text{V}$ $T_A = 25^{\circ}\text{C}$
OUTPUTS	$V_{out(0)}$	Output voltage, logical "0"	2.4		0.4	V	$I_{out} = 1.6\text{mA}$ (into output) See note 3
	$V_{out(1)}$	Output voltage, logical "1"				V	$I_{out} = 0.4\text{mA}$ (out of output) and Figure #1
	I_{out}	Output leakage current	-10		+10	μA	$V_{SS} - 6\text{V} \leq V_{out} \leq V_{SS}$ $T_A = 25^{\circ}\text{C}$ (outputs disabled)
DYNAMIC CHARACTERISTICS	t_{ACC}	Address-to-output access time			600	ns	See timing Section and Figure #1
	t_{OD}	Output delay time			350	ns	
	t_{OEO}	Output enable/disable time		125	300	ns	
	t_{CS}	Chip Select to Output Delay			600	ns	
	t_{CD}	Chip Deselect to Output Delay			600	ns	

*Typical values apply at $V_{SS} = +5.0\text{V}$, $V_{GG} = -12.0\text{V}$, $T_A = 25^{\circ}\text{C}$

- NOTES:**
- Supply voltages shown are for operation in a TTL/DTL system. Other supply voltages may be used if V_{DD} and V_{GG} maintain the same relationship to V_{SS} , e.g., $V_{SS}=0\text{V}$, $V_{DD} = -5\text{V}$, $V_{GG} = -17\text{V}$. Input voltages would also need to be adjusted accordingly.
 - Max measurements at 0°C. (MOS supply currents increase as temperature decreases.) I_{SS} will increase 1.6mA (max) for each input at logic 0 when pull-up resistors are programmed.
 - Unit operated at minimum specified cycle time.
 - The outputs become open circuited when disabled or deselected. As shown in Fig. 1, an output with a "1" expected out does not transition through the 1.5V point when enabled (selected) or disabled (deselected); this is true because the TTL equivalent load pulls the open-circuited output to approximately 2 volts.

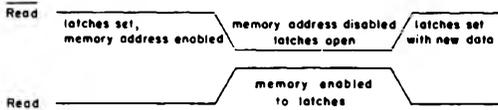
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TIMING

Notes:

1. All times are referenced to the 1.5V point relative to V_{DD} (ground) except rise and fall time measurements.
2. Chip enable = V_{SS} for all measurements except when measuring T_{OEQ} .
3. Logic 0 is defined as V_{DD} or ground; logic 1 as V_{SS} or +5V.

INTERNAL FUNCTION OF READ/READSIGNALS

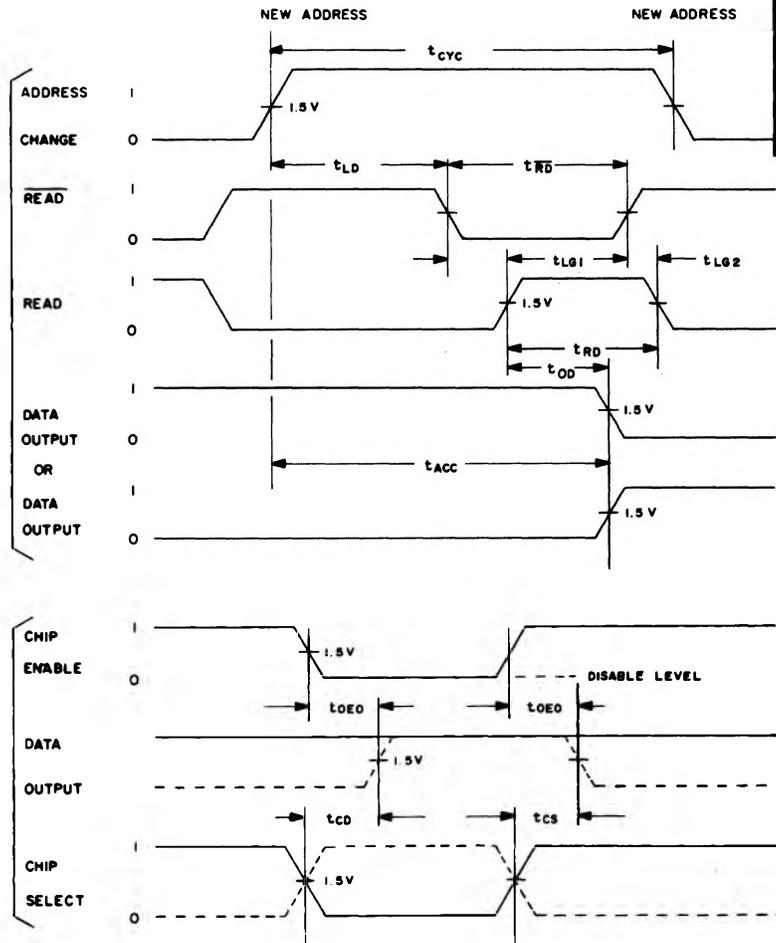


Set up time, t_{id} , allows the input address to propagate through the address decoder and memory matrix prior to READ logic 0 time. As indicated above, READ at a logic 0 internally disables the input address so that an external address change may occur without affecting the location previously selected. The latches are also readied to receive new data which is enabled from the matrix when READ is at a logic 1. Data is set in the latches when READ is allowed to rise back to its logic 1 state. In actual use, the READ rising and falling edges can precede the falling and rising edges of READ, respectively, as implied by the specification of negative read lag times. This allows a very flexible timing relation between the two pulses, in that either input can be the inversion of the other or both may be generated from separate timing circuits.

Output data appears following the rise of the READ pulse but correct output data will not appear until READ has gone low. For this reason, READ is shown preceding READ even though other relationships are allowed. If READ is made to precede READ, delay time, t_{OD} , should be referenced to the fall of READ rather than as shown.

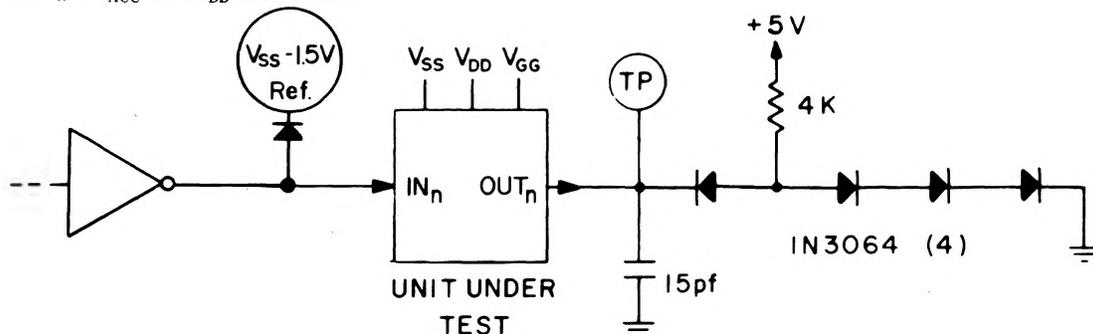
The chip is disabled by applying a logical 0 to the chip enable input, forcing the outputs to an open-circuit condition. The output data present at the time of disable will again be present upon re-enabling unless a new read cycle was initiated for a different address while the chip was disabled, in which case the new data would be present at the outputs.

The programmable 3-bit chip select timing would be the same as the address inputs.



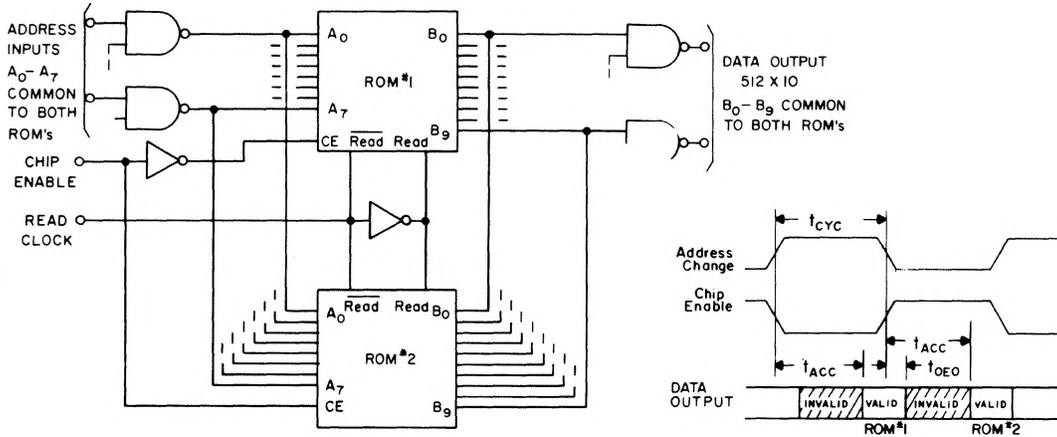
NOTE: Wave forms are not to scale.

FIGURE #1 t_{ACC} and t_{DD} test circuit



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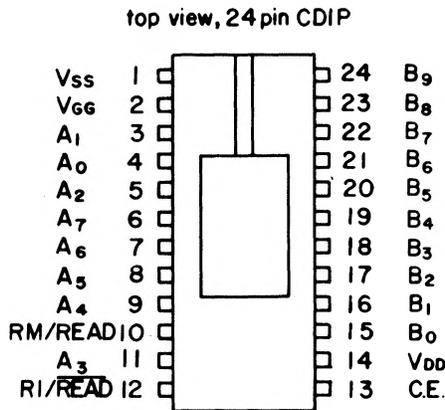
APPLICATIONS



Application shows wire-Or'ing for expansion to a 512 X 10 memory. Further expansion is possible by 1 of N decoding to the Chip Enable input (or with the optional 3-bit decoder) while maintaining the time relationships shown. t_{cyc} should include the desired data-valid time. Interface devices may be TTL or DTL.

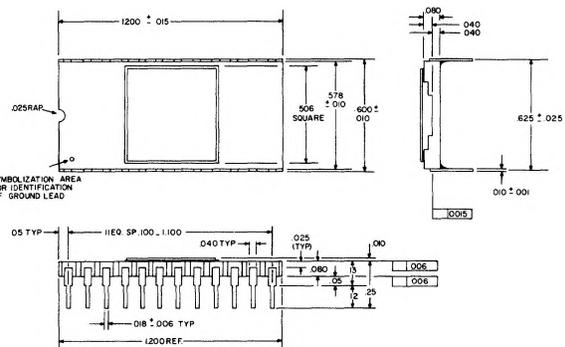
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PIN CONNECTIONS

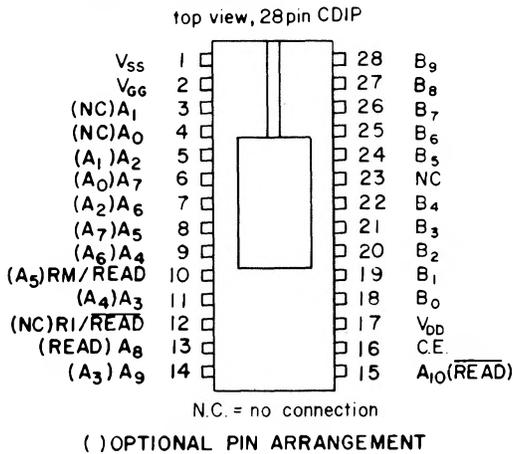


PHYSICAL DESCRIPTION

(24 lead ceramic dual-in-line hermetic package)

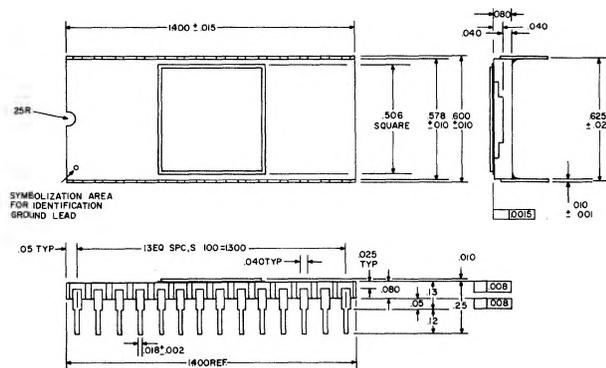


PIN CONNECTIONS



PHYSICAL DESCRIPTION

(28 lead ceramic dual-in-line hermetic package)



MOSTEK ROM PUNCHED-CARD CODING FORMAT¹

MK 2400 P

Cols. Information Field

First Card

1-30 Customer
31-50 Customer Part Number
60-72 Mostek Part Number²

“Negative Logic”
35-57 Verification Code⁷
60-74 Package Choice⁸

Second Card

1-30 Engineer at Customer Site
31-50 Direct Phone Number for Engineer

Data Cards

1-3 Decimal Address
5 Output B9
6 Output B8
7 Output B7
8 Output B6
9 Output B5
10 Output B4
11 Output B3
12 Output B2
13 Output B1
14 Output B0
16 Octal Equivalent of: B9⁹
17 Octal Equivalent of: B8, B7, B6⁹
18 Octal Equivalent of: B5, B4, B3⁹
19 Octal Equivalent of: B2, B1, B0⁹

Third Card

1-5 Mostek Part Number²
10-16 Organization³
29 A8⁴
30 A9⁴
31 A10⁴
32 Pull-up Resistor⁵

Fourth Card

0-6 Data Format⁴ — “MOSTEK”
15-28 Logic — “Positive Logic” or

Notes: 1. Positive or negative logic formats are accepted as noted in the fourth card.

2. Assigned by Mostek Marketing Department; may be left blank.

3. Punched as 0256x10.

4. A “0” indicates the chip is enabled by a logic 0, a “1” indicates it is enabled by a logic 1, and a “2” indicates a “Don’t Care” condition.

5. A “1” indicates pull-ups; a “0” indicates no pull-ups.

6. “MOSTEK” format only is accepted on this part.

7. Punched as: (a) VERIFICATION HOLD — i.e. customer verification of the data as reproduced by MOSTEK is required prior to production of the ROM. To accomplish this MOSTEK supplies a copy of its Customer Verification Data Sheet (CVDS) to the customer.

(b) VERIFICATION PROCESS — i.e. the customer will receive a CVDS but production will begin prior to receipt of customer verification.

(c) VERIFICATION NOT NEEDED — i.e. the customer will not receive a CVDS and production will begin immediately.

8. “24 PIN”, “28 PIN STANDARD”, or “28 PIN OPTIONAL” (left justified to column 60).

9. The octal parity check is created by breaking up the output word into groups of three from right to left and creating a base 8 (octal) number in place of these groups. For example the output word 1010011110 would be separated into groups 1/010/011/110 and the resulting octal equivalent number is 1236.